

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLV59** is a Common Emitter Device Designed for Class A and AB Amplifier Applications in TV Band IV-V Transmitters.

FEATURES INCLUDE:

- Gold Metalization
- Intrnal Matching
- Emitter Ballasting

MAXIMUM RATINGS

I_C	10 A
V_{CB}	50 V
P_{DISS}	80 W @ $T_C = 25^\circ C$
T_J	$-55^\circ C$ to $+200^\circ C$
T_{STG}	$-55^\circ C$ to $+150^\circ C$
θ_{JC}	2.2 $^\circ C/W$

PACKAGE STYLE .230 6FLG.				
Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	24.64	24.89	0.970	0.980
B	5.72	5.96	0.225	0.235
C	6.10	6.60	0.240	0.260
D	2.93	3.17	0.115	0.125
E	2.72	2.97	0.107	0.117
G	4.33	5.33	0.190	0.210
H	4.07	4.57	0.160	0.180
J	0.11	0.15	0.004	0.006
K	10.30	11.43	0.425	0.450
M	45 NOM		45 NOM	
N	9.02	9.77	0.355	0.385
Q	3.05	3.30	0.120	0.130
U	18.29	18.54	0.720	0.730

1, 3, 4 & 6 = EMITTER
2 = BASE 5 = COLLECTOR

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50 \text{ mA}$			25			V
BV_{CES}	$I_C = 50 \text{ mA}$			50			V
BV_{EBO}	$I_E = 20 \text{ mA}$			4.0	5.0		V
h_{FE}	$V_{CE} = 5.0 \text{ V}$	$I_C = 1.0 \text{ A}$		20		100	---
C_{OB}	$V_{CB} = 28 \text{ V}$	$f = 1.0 \text{ MHz}$			50		pF
P_G	$V_{CE} = 25 \text{ V}$	$I_{CQ} = 60 \text{ mA}$	$P_{OUT} = 30.0 \text{ W}$	8.0	9.0		dB
IMD_3	Vision = -8.0 dB	Sound = -10 dB	Chroma = -16 dB		-48		dBc
P_G	$V_{CE} = 25 \text{ V}$	$I_{CQ} = 1.6 \text{ A}$	$P_{OUT} = 15 \text{ W}$	9	10		dB
IMD_3	Vision = -8.0 dB	Sound = -10 dB	Chroma = -16 dB		-60		dBc